- 1 1. A method comprising:
- 2 enabling a phase change memory to be both
- 3 optically and electrically accessed.
- 1 2. The method of claim 1 including forming a phase
- 2 change memory with a pair of parallel spaced electrodes and
- 3 a phase change material between said electrodes.
- 1 3. The method of claim 2 including arranging said
- 2 phase change material and said electrodes laterally.
- 1 4. The method of claim 3 including enabling light
- 2 exposure of said phase change material.
- 1 5. The method of claim 4 including enabling light
- 2 exposure through a thermally insulating material.
- 1 6. The method of claim 3 including enabling said
- 2 phase change material to be electrically accessed through
- 3 rows and columns.
- 7. The method of claim 6 including locating said
- 2 rows and columns to enable light access to said cells.
- 1 8. The method of claim 7 including positioning one
- 2 of said rows and columns below said phase change material.

- 1 9. The method of claim 8 including providing a via
- 2 coupling one of said electrodes to said underlying row or
- 3 column.
- 1 10. The method of claim 1 including using a phase
- 2 change memory to convert an optical signal to an electrical
- 3 signal.
- 1 11. The method of claim 1 including using a phase
- 2 change memory to convert an electrical signal to an optical
- 3 signal.
- 1 12. A memory comprising:
- a light accessible phase change material; and
- a circuit to electrically access said phase
- 4 change material.
- 1 13. The memory of claim 12 wherein said phase change
- 2 material is a chalcogenide.
- 1 14. The memory of claim 12 wherein said phase change
- 2 material is arranged laterally and includes a pair of
- 3 laterally spaced electrodes approximate to each of two
- 4 opposed ends of said material.

- 1 15. The memory of claim 14 including rows and
- 2 columns, said rows and columns arranged to avoid blocking
- 3 light access to said phase change material.
- 1 16. The memory of claim 15 wherein one of said rows
- 2 and columns is arranged beneath said phase change material.
- 1 17. The memory of claim 16 including a via which
- 2 extends from one of said electrodes to said underlying row
- 3 or column.
- 1 18. The memory of claim 12 including a substantially
- 2 light transmissive thermally insulating material over said
- 3 phase change material.
- 1 19. The memory of claim 18 wherein said substantially
- 2 light transmissive, thermally insulating material is oxide.
- 1 20. The memory of claim 12 including a micro-mirror
- 2 to optically access said phase change memory material.
- 1 21. The memory of claim 11 including a plurality of
- 2 cells each including phase change material, and an optical
- 3 system to individually expose one memory cell of the
- 4 plurality of memory cells to a laser light.

- 1 22. The memory of claim 12 wherein said circuit
- 2 includes an addressing circuit.
- 1 23. A system comprising:
- 2 a processor-based device;
- a wireless interface coupled to said processor-
- 4 based device; and
- a semiconductor memory coupled to said device,
- 6 said memory including a light accessible phase change
- 7 material and a circuit to electrically access said phase
- 8 change material.
- 1 24. The system of claim 23 wherein said phase change
- 2 material is a chalcogenide.
- 1 25. The system of claim 23 including a pair of spaced
- 2 electrodes, said phase change material positioned between
- 3 said spaced electrodes.
- 1 26. The system of claim 25 including a substrate,
- 2 said phase change material positioned over said substrate
- 3 such that the length of said phase change material is
- 4 generally parallel to said substrate.
- 1 27. The system of claim 26 including a first set of
- 2 conductors and a second set of conductors, said second set

- 3 of conductors being generally transverse to said first set
- 4 of conductors.
- 1 28. The system of claim 27 wherein said first and
- 2 second set of conductors arranged to avoid blocking light
- 3 access to said phase change material.
- 1 29. The system of claim 28 wherein one of said sets
- 2 of conductors is arranged beneath said phase change
- 3 material.
- 1 30. The system of claim 29 wherein a via extends from
- 2 one of said electrodes to an underlying conductor.
- 1 31. The system of claim 23 including a substantially
- 2 light transmissive material over said phase change
- 3 material.
- 1 32. A method comprising:
- 2 optically accessing a phase change memory
- 3 material; and
- 4 electrically accessing the phase change memory
- 5 material.

- 1 33. The method of claim 32 including forming a phase
- 2 change memory with a pair of parallel spaced electrodes and
- 3 a phase change material between said electrodes.
- 1 34. The method of claim 33 including arranging said
- 2 phase change material and said electrodes laterally.
- 1 35. The method of claim 34 including enabling light
- 2 exposure of said phase change material.
- 1 36. The method of claim 35 including enabling light
- 2 exposure through a thermally insulating material.